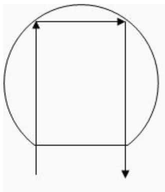
Part Number	Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	5.0	Overall Thickness	250.00 +/- 5.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<2.00µm	Guaranteed by Process
	7.0	Bow	<50.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<50.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	250.00 +/- 5.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	PHOS	Wafer Vendor
	16.0	Handle Resistivity	10-25 Ohmcm	Wafer Vendor
OverallWafer	17.0	Back Surface Quality	Polished with lasermarking	Wafer Vendor
DeviceSilicon	18.0	LPD Count	<30.00pces	@0.3um, Tencor 6220 particle counter
	19.0	Scratches	0	Bright Light, 100% (note 2)
	20.0	Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

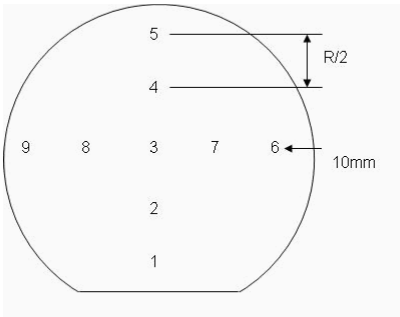
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information